Accepted Manuscript

Compositional Accuracy of Atom Probe Tomography Measurements in GaN: Impact of Experimental Parameters and Multiple Evaporation Events

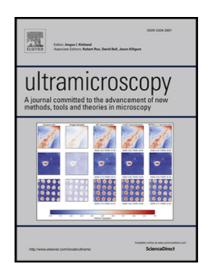
E. Di Russo, I. Blum, J. Houard, M. Gilbert, G. Da Costa, D. Blavette, L. Rigutti

PII: S0304-3991(17)30465-5 DOI: 10.1016/j.ultramic.2018.02.001

Reference: ULTRAM 12529

To appear in: *Ultramicroscopy*

Received date: 9 November 2017 Revised date: 31 January 2018 Accepted date: 3 February 2018



Please cite this article as: E. Di Russo, I. Blum, J. Houard, M. Gilbert, G. Da Costa, D. Blavette, L. Rigutti, Compositional Accuracy of Atom Probe Tomography Measurements in GaN: Impact of Experimental Parameters and Multiple Evaporation Events, *Ultramicroscopy* (2018), doi: 10.1016/j.ultramic.2018.02.001

This is a PDF file of an unedited manuscript that has been accepted for publication. As a service to our customers we are providing this early version of the manuscript. The manuscript will undergo copyediting, typesetting, and review of the resulting proof before it is published in its final form. Please note that during the production process errors may be discovered which could affect the content, and all legal disclaimers that apply to the journal pertain.

ACCEPTED MANUSCRIPT

Highlights:

- The composition of GaN measured by Atom Probe is biased.
- The main parameter influencing the compositional bias is the surface electric field.
- The deficiency of Ga at high field is interpreted in terms of preferential evaporation.
- The deficiency of N at low field is investigated through the study of multiple evaporation events.
- The detected dissociation of molecular ions can produce neutral N, but in moderate quantities.
- Further mechanisms of neutral N production are proposed.

Download English Version:

https://daneshyari.com/en/article/8037721

Download Persian Version:

https://daneshyari.com/article/8037721

<u>Daneshyari.com</u>